REMARKS

Claims 16, 25, 30, 44-49, 54 and 59 have been amended. No new claims have been added. Claims 1-60 are pending.

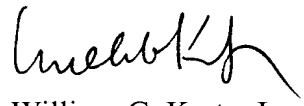
A marked-up version of the changes made to the claims is enclosed herewith as "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

The above amendments to the claims have been made to correct the multiple dependency of the above-listed claims. It is respectfully submitted that purpose of the amendments incorporated herein are to better place the application in condition for examination.

In the event that any additional fees are due in connection with this paper, please charge our Deposit Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, WESTERMAN, HATTORI
McLELAND & NAUGHTON, LLP



William G. Kratz, Jr.
Attorney for Applicants
Reg. No. 22,631

Enclosures: Version With Markings to Show Changes Made
Amendment Transmittal (w/ appropriate fees)

Attorney Docket No.: **010819**
1725 K Street, N.W.
Suite 1000
Washington, D.C. 20006
Tel: (202) 659-2930
WGK/sdj

Q:\FLOATERS\WGK\010819 Preliminary Amendment

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IN THE CLAIMS:

Claims 16, 25, 30, 44-49, 54 and 59 have been amended as follows:

16. (Amended) A method of manufacturing a device comprising the steps of:

detecting defects on a wafer using an inspection apparatus according to any one of claims 1 to ~~15~~ 5 in the middle of a process or subsequent to the process.

25. (Amended) A defect inspection apparatus using the E x B separator defined by any of claims 21 to ~~24~~ 23, in which:

either one of said first charged particle beam or said second charged particle beam is a primary sample to be inspected, and the other is a secondary charged particle beam generated from said sample by the irradiation of said primary charged particle beam.

30. (Amended) A method for manufacturing a device using an inspection apparatus defined by any one of claims 26 ~~to 29~~ or 27, in which a pattern inspection is performed in the device manufacturing processes.

44. (Amended) A charged particle beam apparatus in accordance with either of claim 41 ~~to 43~~ or 42, in which said dividers are arranged in two locations in the proximity of the charged particle beam irradiating location and the proximity of the hydrostatic bearing.

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45. (Amended) A charged particle beam apparatus in accordance with ~~any~~ either of ~~claims~~ claim 41 ~~to 44~~ or 42, in which the gas supplied to the hydrostatic bearing of said stage is nitrogen or an inert gas.

46. (Amended) A charged particle beam apparatus in accordance with ~~any~~ either of ~~claims~~ claim 41 ~~to 45~~ or 42, in which a surface treatment is applied to at least the surface of a part facing the hydrostatic bearing in said XY stage so as to reduce the amount of gas to be desorbed.

47. (Amended) A wafer defect inspection apparatus for inspecting the surface of a wafer for defects by using the apparatus disclosed in ~~any~~ either of ~~claims~~ claim 41 ~~to 46~~ or 42.

48. (Amended) An exposing apparatus for delineating the circuit pattern of a semiconductor device on the surface of a semiconductor wafer or a reticle by using the apparatus disclosed in ~~any~~ either of ~~claims~~ claim 41 ~~to 46~~ or 42.

49. (Amended) A semiconductor manufacturing method for manufacturing a semiconductor by using the apparatus disclosed in ~~any~~ either of ~~claims~~ claim 41 ~~to 48~~ or 42.

54. (Amended) A semiconductor manufacturing method including a process for inspecting a finished wafer or ~~an~~ a wafer under processing for defects by using an inspection apparatus in accordance with any of claims 50 to ~~53~~ 52.

59. (Amended) A semiconductor manufacturing method for manufacturing a semiconductor by using the apparatus in accordance with either of claims 55 ~~to 58~~ or 56.